

MITSUBISHI IGBT MODULES

CM200RL-12NF

HIGH POWER SWITCHING USE

CM200RL-12NF



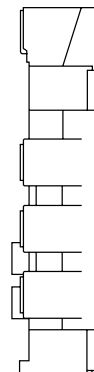
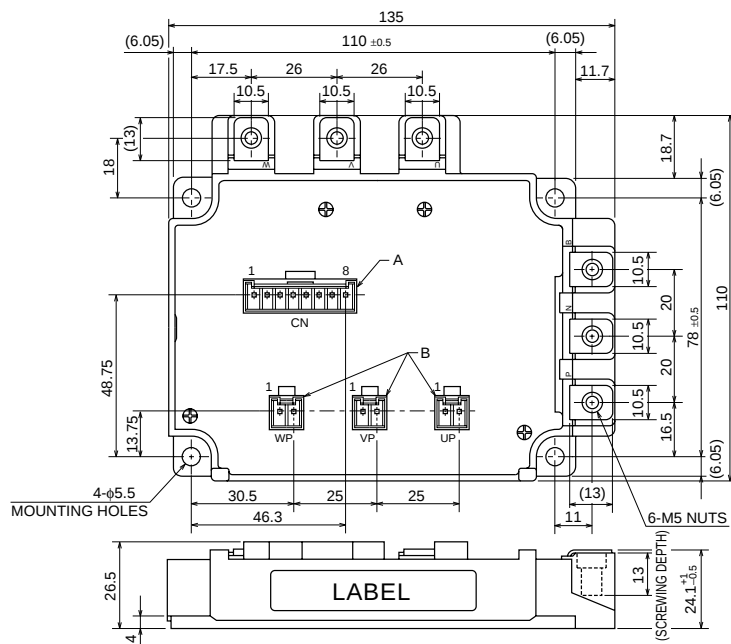
- IC200A
- VCES600V
- Insulated Type
- 7-elements in a pack

APPLICATION

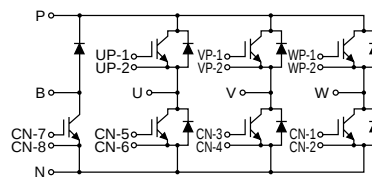
AC drive inverters & Servo controls, etc

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



Housing Type of A and B
(J.S.T.Mfg.Co.Ltd)
A = B8P-VH-FB-B, B = B2P-VH-FB-B



CIRCUIT DIAGRAM

CM200RL-12NF

HIGH POWER SWITCHING USE

ABSOLUTE MAXIMUM RATINGS ($T_j = 25^\circ\text{C}$)

INVERTER PART

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	G-E Short	600	V
V_{GES}	Gate-emitter voltage	C-E Short	± 20	V
I_C	Collector current	DC, $T_c = 88^\circ\text{C}^{*1}$	200	A
I_{CM}		Pulse (Note 2)	400	A
I_E (Note 1)	Emitter current		200	A
I_{EM} (Note 1)		Pulse (Note 2)	400	A
P_C (Note 3)	Maximum collector dissipation	$T_c = 25^\circ\text{C}$	890	W

BRAKE PART

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	G-E Short	600	V
V_{GES}	Gate-emitter voltage	C-E Short	± 20	V
I_C	Collector current	DC, $T_c = 99^\circ\text{C}^{*1}$	100	A
I_{CM}		Pulse (Note 2)	200	A
P_C (Note 3)	Maximum collector dissipation	$T_c = 25^\circ\text{C}$	540	W
V_{RRM}	Repetitive peak reverse voltage	Clamp diode part	600	V
I_{FM}	Forward current	Clamp diode part	100	A

(COMMON RATING)

Symbol	Parameter	Conditions	Ratings	Unit
T_j	Junction temperature		$-40 \sim +150$	$^\circ\text{C}$
T_{stg}	Storage temperature		$-40 \sim +125$	$^\circ\text{C}$
V_{iso}	Isolation voltage	Main Terminal to base plate, AC 1 min.	2500	V
—	Torque strength	Main Terminal M5	2.5 ~ 3.5	N • m
—		Mounting holes M5	2.5 ~ 3.5	N • m
—	Weight	Typical value	750	g

CM200RL-12NF

HIGH POWER SWITCHING USE

ELECTRICAL CHARACTERISTICS (T_j = 25°C) INVERTER PART

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA
VGE(th)	Gate-emitter threshold voltage	IC = 20mA, VCE = 10V	6	7	8	V
IGES	Gate leakage current	VGE = VGES, VCE = 0V	—	—	0.5	μA
VCE(sat)	Collector-emitter saturation voltage	IC = 200A, VGE = 15V T _j = 25°C T _j = 125°C	—	1.7 1.7	2.2 —	V
Cies	Input capacitance	VCE = 10V VGE = 0V	—	—	30	nF
Coēs	Output capacitance		—	—	3.7	nF
Cres	Reverse transfer capacitance		—	—	1.2	nF
QG	Total gate charge	VCC = 300V, IC = 200A, VGE = 15V	—	800	—	nC
td(on)	Turn-on delay time	VCC = 300V, IC = 200A VGE1 = VGE2 = 15V RG = 3.1Ω, Inductive load switching operation IE = 200A	—	—	120	ns
tr	Turn-on rise time		—	—	100	ns
td(off)	Turn-off delay time		—	—	300	ns
tr	Turn-off fall time		—	—	300	ns
t _{rr} (Note 1)	Reverse recovery time		—	—	150	ns
Q _{rr} (Note 1)	Reverse recovery charge		—	4.8	—	μC
VEC(Note 1)	Emitter-collector voltage	IE = 200A, VGE = 0V	—	—	2.8	V
R _{th(j-c)Q}	Thermal resistance	IGBT part (1/6 module)* ¹	—	—	0.14	°C/W
R _{th(j-c)R}		FWDi part (1/6 module)* ¹	—	—	0.22	°C/W
R _{th(c-f)}	Contact thermal resistance	Case to fin, Thermal compound Applied (1/6 module)* ²	—	0.051	—	°C/W
RG	External gate resistance		3.1	—	31	Ω

BRAKE PART

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
ICES	Collector cutoff current	VCE = VCES, VGE = 0V	—	—	1	mA
VGE(th)	Gate-emitter threshold voltage	IC = 10mA	6	7	8	V
IGES	Gate leakage current	VGE = VGES, VCE = 0V	—	—	0.5	μA
VCE(sat)	Collector-emitter saturation voltage	IC = 100A, VGE = 15V T _j = 25°C T _j = 125°C	—	1.7 1.7	2.2 —	V
Cies	Input capacitance	VCE = 10V VGE = 0V	—	—	15	nF
Coēs	Output capacitance		—	—	1.9	nF
Cres	Reverse transfer capacitance		—	—	0.6	nF
QG	Total gate charge	VCC = 300V, IC = 100A, VGE = 15V	—	400	—	nC
VFM	Forward voltage drop	IF = 100A	—	—	2.8	V
R _{th(j-c)Q}	Thermal resistance	IGBT part* ¹	—	—	0.23	°C/W
R _{th(j-c)R}		Clamp diode part* ¹	—	—	0.41	°C/W
RG	External gate resistance		6.3	—	63	Ω

*1 : T_c measured point is just under the chips.

If you use this value, R_{th(f-a)} should be measured just under the chips.

*2 : Typical value is measured by using Shin-etsu Silicone "G-746".

Note 1. IE, VEC, t_{rr} & Q_{rr} represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temp. (T_j) does not exceed T_{jmax} rating.

3. Junction temperature (T_j) should not increase beyond 150°C.

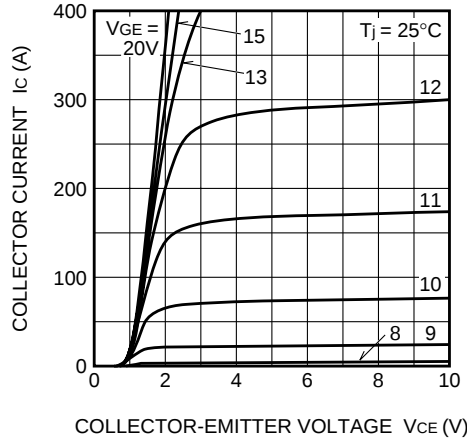
4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

CM200RL-12NF

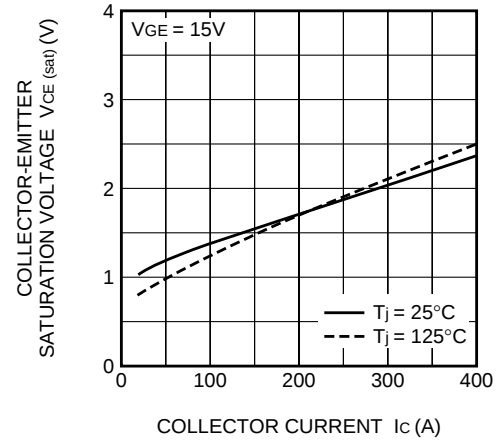
HIGH POWER SWITCHING USE

PERFORMANCE CURVES

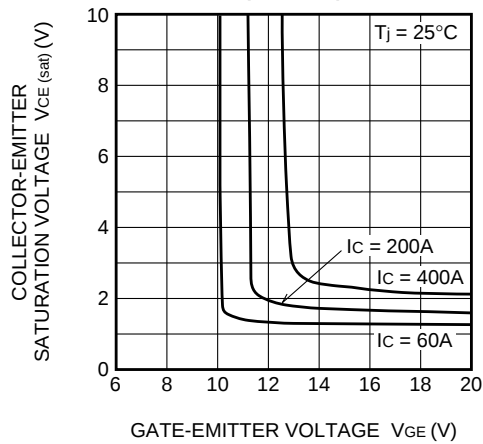
OUTPUT CHARACTERISTICS
(TYPICAL)



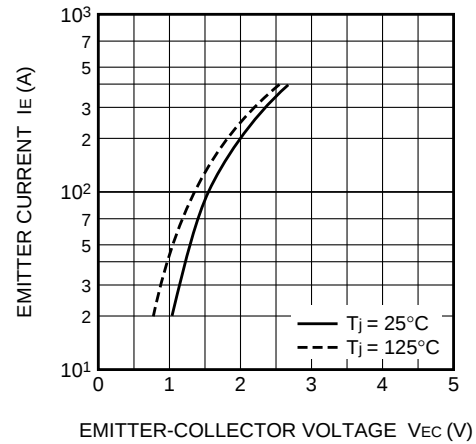
COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)



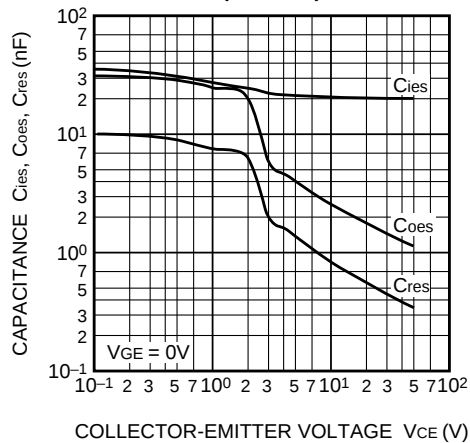
COLLECTOR-EMITTER SATURATION
VOLTAGE CHARACTERISTICS
(TYPICAL)



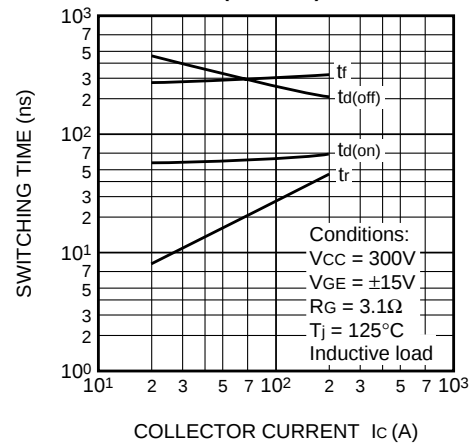
FREE-WHEEL DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



CAPACITANCE- V_{CE}
CHARACTERISTICS
(TYPICAL)



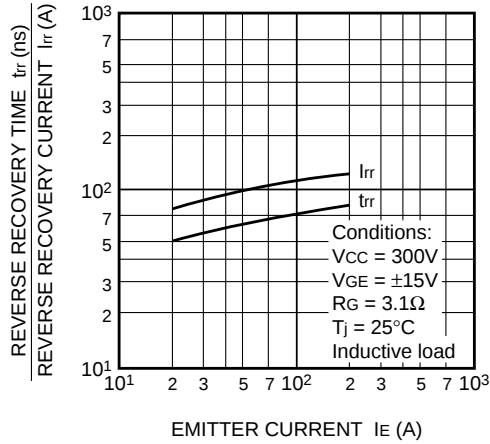
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)



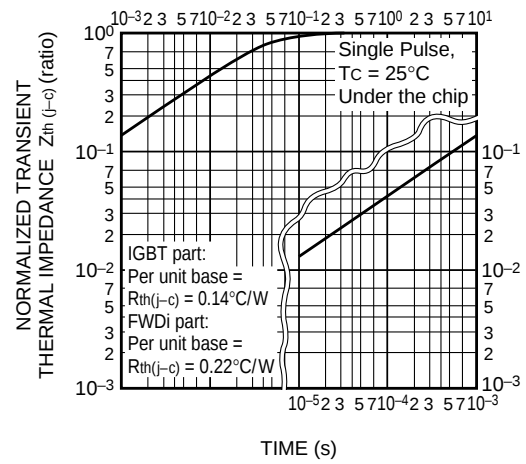
CM200RL-12NF

HIGH POWER SWITCHING USE

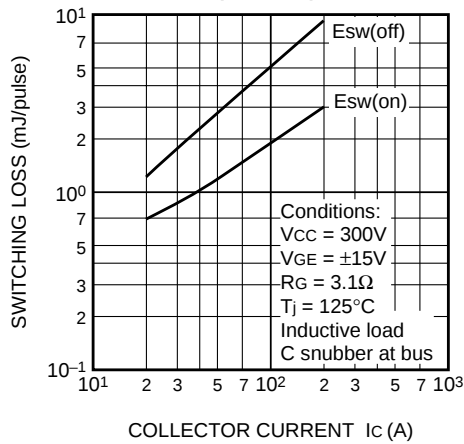
**REVERSE RECOVERY CHARACTERISTICS
OF FREE-WHEEL DIODE
(TYPICAL)**



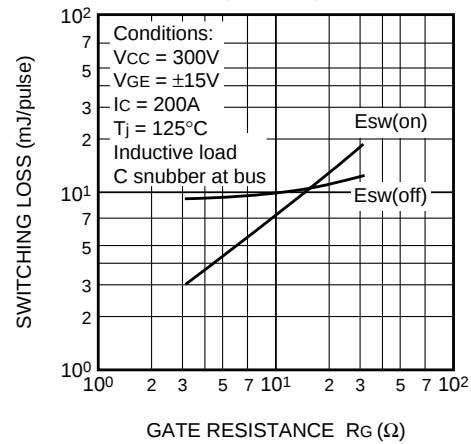
**TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(IGBT part & FWDi part)**



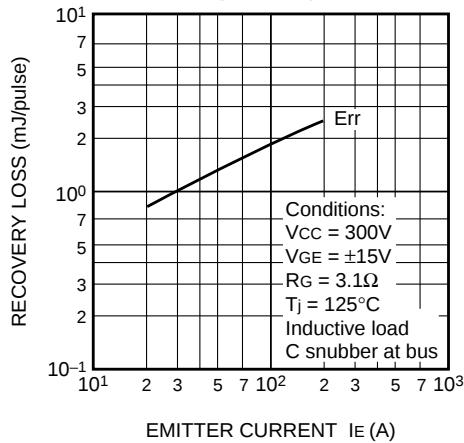
**SWITCHING LOSS vs.
COLLECTOR CURRENT
(TYPICAL)**



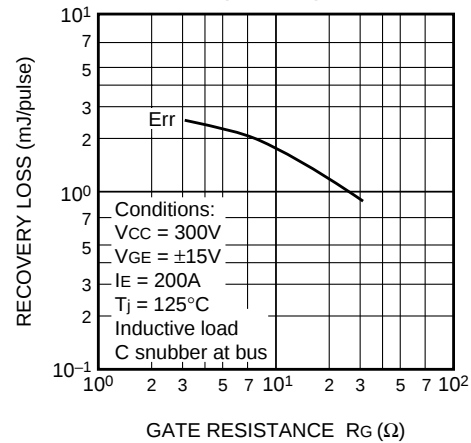
**SWITCHING LOSS vs.
GATE RESISTANCE
(TYPICAL)**



**RECOVERY LOSS vs. Ie
(TYPICAL)**



**RECOVERY LOSS vs.
GATE RESISTANCE
(TYPICAL)**



CM200RL-12NF

HIGH POWER SWITCHING USE

